

Thyristor Modules PSKT 225 Thyristor/Diode Modules PSKH 225

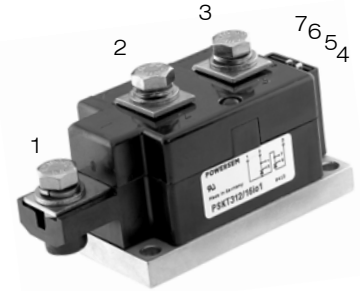
$$I_{TRMS} = 2x 400 A$$

$$I_{TAVM} = 2x 221 A$$

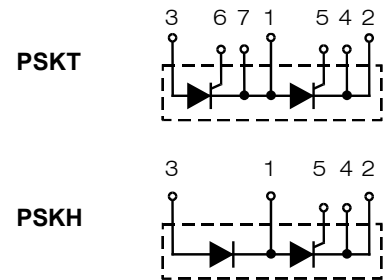
$$V_{RRM} = 1200-1800 V$$

Preliminary Data Sheet

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
1300	1200	PSKT 225-12io1 PSKH 225-12io1
1500	1400	PSKT 225-14io1 PSKH 225-14io1
1700	1600	PSKT 225-16io1 PSKH 225-16io1
1900	1800	PSKT 225-18io1 PSKH 225-18io1



Symbol	Test Conditions	Maximum Ratings
I_{TRMS} I_{TAVM}	$T_{VJ} = T_{VJM}$ $T_C = 85^\circ C$; 180° sine	400 A 221 A
$I_{TSM}^{\dagger} I_{FSM}$	$T_{VJ} = 45^\circ C$; $V_R = 0$	t = 10 ms (50 Hz) 8000 A t = 8.3 ms (60 Hz) 8500 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz) 7000 A t = 8.3 ms (60 Hz) 7700 A
$\int i^2 dt$	$T_{VJ} = 45^\circ C$ $V_R = 0$	t = 10 ms (50 Hz) 320 000 A ² s t = 8.3 ms (60 Hz) 300 000 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz) 245 000 A ² s t = 8.3 ms (60 Hz) 246 000 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ f = 50 Hz, $t_p = 200 \mu s$ $V_D = 2/3 V_{DRM}$ $I_G = 1 A$, $di_G/dt = 1 A/\mu s$	repetitive, $I_T = 750 A$ 100 A/ μs non repetitive, $I_T = I_{TAVM}$ 500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	1000 V/ μs
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu s$ 120 W $t_p = 500 \mu s$ 60 W 20 W 10 V
P_{GAV} V_{RGM}		
T_{VJ}		-40...+130 °C
T_{VJM}		130 °C
T_{stg}		-40...+125 °C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 mA$	t = 1 min 3000 V~ t = 1 s 3600 V~
M_d	Mounting torque (M6) Terminal connection torque (M8)	4.5-7/40-62 Nm/lb.in. 11-13/97-115 Nm/lb.in.
Weight	Typical including screws	750 g



Features

- International standard package
- Direct copper bonded Al₂O₃-ceramic with copper base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered E 148688
- Keyed gate/cathode twin pins

Applications

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

Advantages

- Simple mounting
- Improved temperature and power cycling capability
- Reduced protection circuits

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

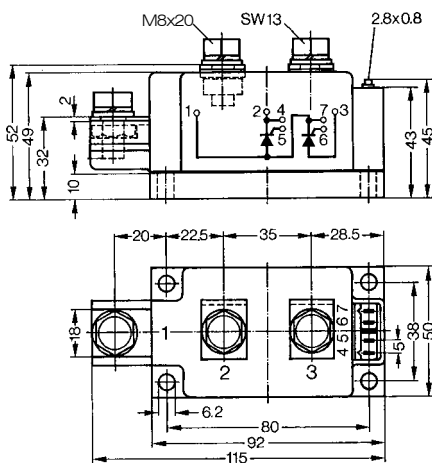
Symbol	Test Conditions	Characteristic Values
I_{RRM}, I_{DRM}	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	40 mA
V_T, V_F	$I_T, I_F = 600 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.40 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 130^\circ\text{C}$)	0.8 V
r_T		0.76 m Ω
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	2 V
	$T_{VJ} = -40^\circ\text{C}$	3 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	150 mA
	$T_{VJ} = -40^\circ\text{C}$	220 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.25 V
I_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	10 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 30 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	200 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	150 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 1 \text{ A}; di_G/dt = 1 \text{ A}/\mu\text{s}$	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 300 \text{ A}; t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 50 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ. 200 μs
Q_s	$T_{VJ} = 125^\circ\text{C}; I_T, I_F = 300 \text{ A}; -di/dt = 50 \text{ A}/\mu\text{s}$	550 μC
I_{RM}		235 A
R_{thJC}	per thyristor (diode); DC current	0.157 KW
	per module	0.08 KW
R_{thJK}	per thyristor (diode); DC current	0.197 KW
	per module	0.1 KW
d_s	Creeping distance on surface	12.7 mm
d_A	Creepage distance in air	9.6 mm
a	Maximum allowable acceleration	50 m/s ²

Optional accessories for modules

Keyed Gate/Cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red
 Type **ZY 180 L** (L = Left for pin pair 4/5) } UL 758, style 1385,
 Type **ZY 180 R** (R = Right for pin pair 6/7) } CSA class 5851, guide 460-1-1

Dimensions in mm (1 mm = 0.0394")

PSKT



PSKH

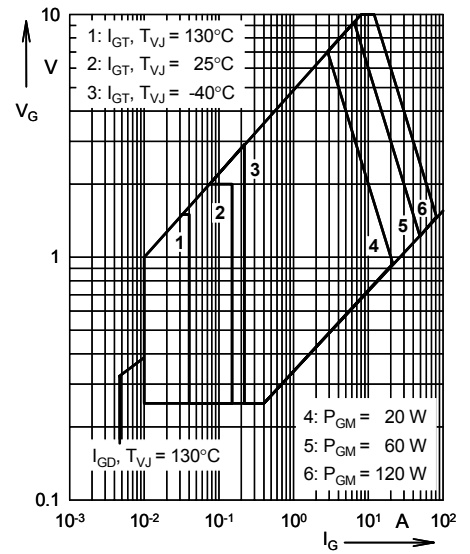
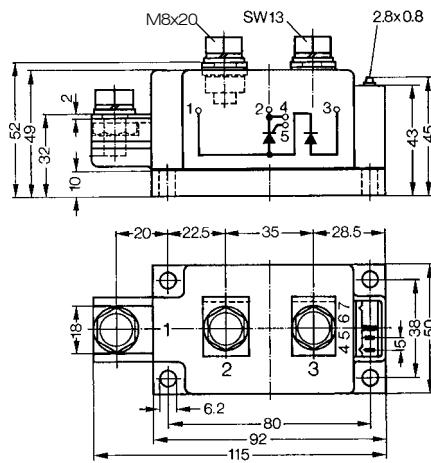


Fig. 1 Gate trigger characteristics

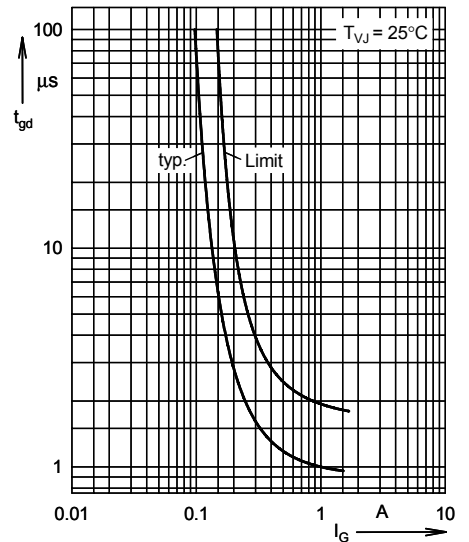


Fig. 2 Gate trigger delay time

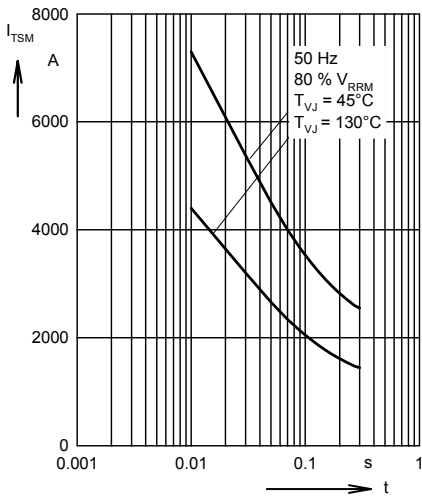


Fig. 3 Surge overload current
 I_{TSM} , I_{FSM} : Crest value, t : duration

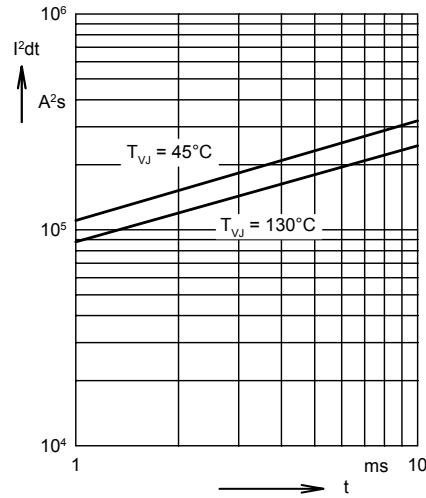


Fig. 4 $\int i^2 dt$ versus time (1-10 ms)

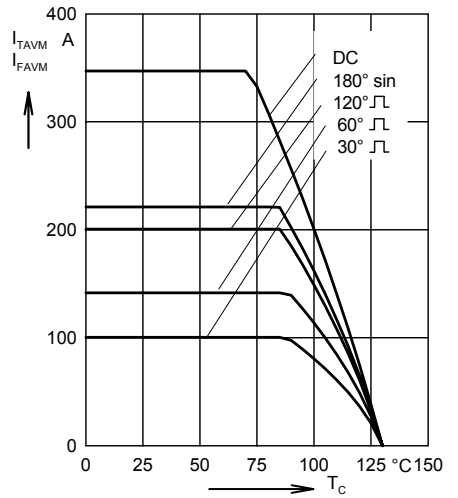


Fig. 4a Maximum forward current at case temperature

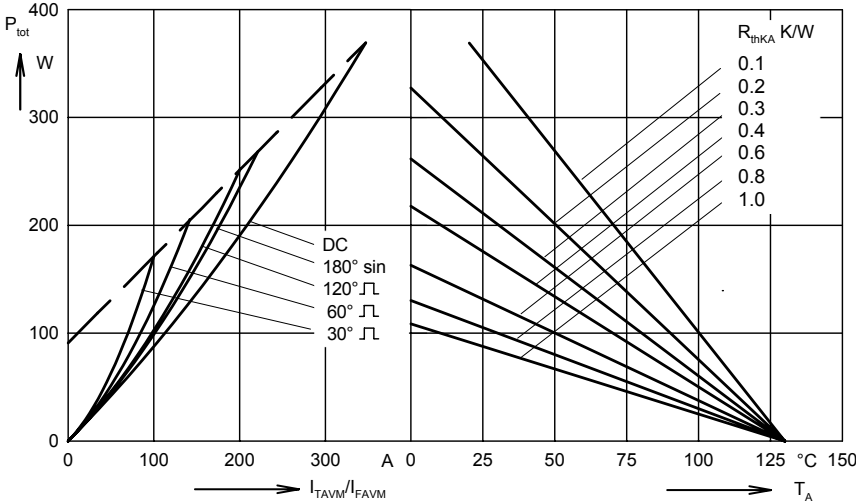


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

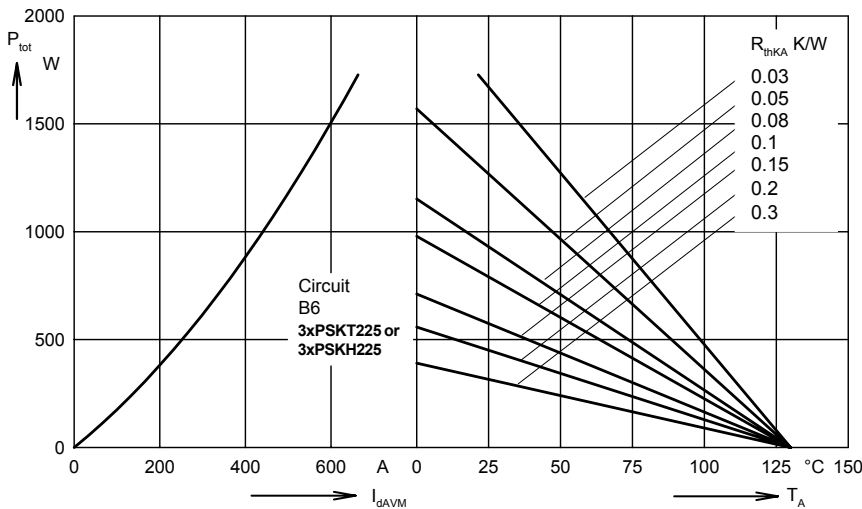


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

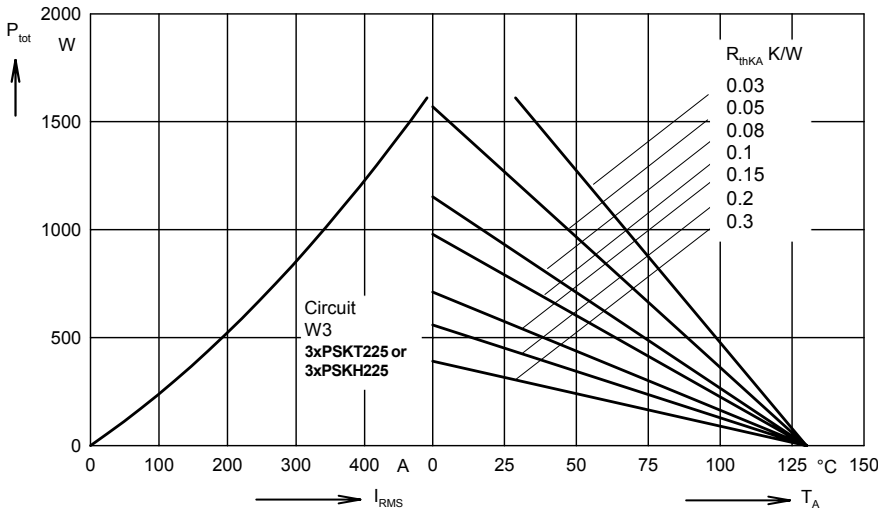


Fig. 7 Three phase AC-controller:
Power dissipation versus RMS
output current and ambient
temperature

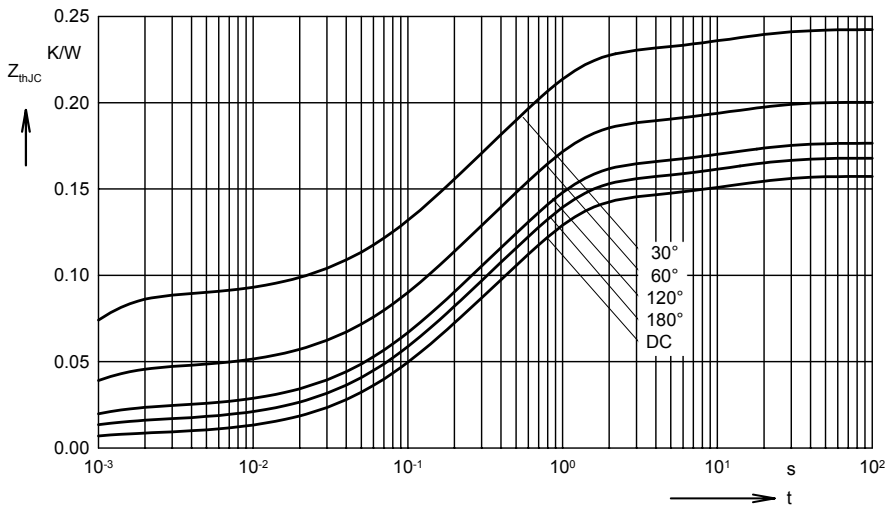


Fig. 8 Transient thermal impedance
junction to case (per thyristor or
diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.157
180°	0.168
120°	0.177
60°	0.200
30°	0.243

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0076	0.00054
2	0.0406	0.098
3	0.0944	0.54
4	0.0147	12

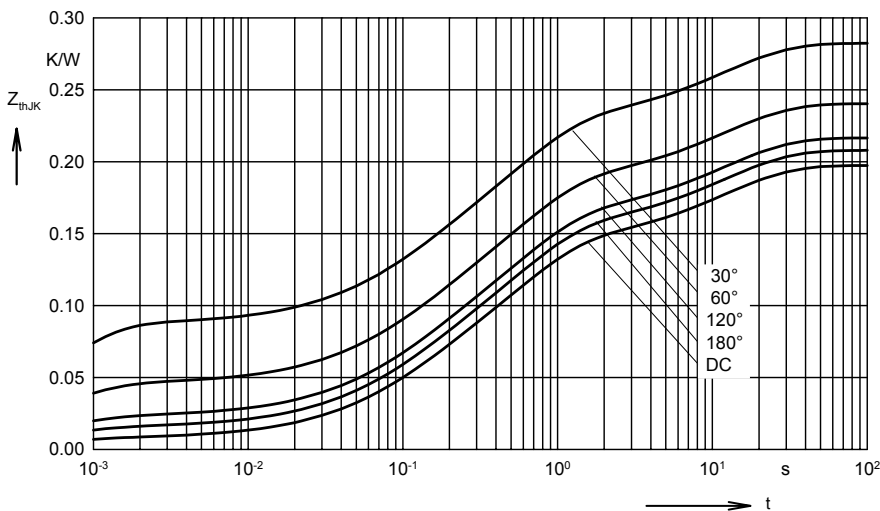


Fig. 9 Transient thermal impedance
junction to heatsink (per thyristor
or diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.197
180°	0.208
120°	0.217
60°	0.240
30°	0.283

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0076	0.00054
2	0.0406	0.098
3	0.0944	0.54
4	0.0147	12
5	0.04	12